INA28x-Q1 汽车级、–14V 至 +80V、双向、高精度、低侧/高侧、电压输出、分流监控器

1 特性

- 符合汽车 应用标准
- 具有符合 AEC-Q100 标准的下列结果
  - 器件温度 1 级：–40°C 至 +125℃ 环境工作温度范围
  - 器件人体放电模式 (HBM) 静电放电 (ESD) 分类等级 H2
  - 器件组件充电模式 (CDM) ESD 分类等级 C5
- 宽共模电压范围：-14V 至 +80V
- 偏移电压：±20μV
- 共模抑制比 (CMRR)：140dB
- 精度：
  - ±1.4% 增益误差（最大值）
  - 0.3μV/°C 偏移漂移
  - 0.005%/°C 增益漂移（最大值）
- 可用的增益：
  - 50 V/V：INA282-Q1
  - 100 V/V：INA286-Q1
  - 200 V/V：INA283-Q1
  - 500 V/V：INA284-Q1
  - 1000 V/V：INA285-Q1
- 静态电流：900μA（最大值）

2 应用

- 电动车 (EV) 和混合动力汽车 (HEV) 电池管理
- EV 和 HEV 充电器
- 电动助力转向 (EPS) 系统
- 车身控制模块
- 刹车系统
- 电子稳定性控制 (ESC) 系统

3 说明

INA28x-Q1 系列包括 INA282-Q1、INA283-Q1、INA284-Q1、INA285-Q1 和 INA286-Q1 器件。这些器件是电压输出分流监控器，能够在 -14V 至 +80V 范围内的共模电压下感测分流器两端的压降，与电源电压无关。零漂移架构的低偏移使得电流感测的分流器两端的最大压降低至 10 mV 的满量程。

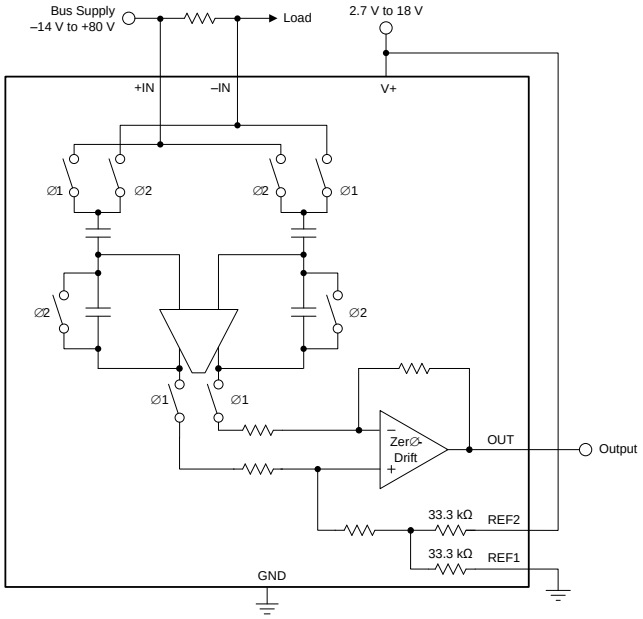
这些电流感测放大器可由电压为 2.7V 至 18V 的单电源供电，最大电源电流消耗为 900μA。这些器件的额定扩展工作温度范围为 -40°C 至 +125°C，并且采用 SOIC-8 和 VSSOP-8 封装。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
INA28xAQDRQ1	SOIC (8)	4.90mm x 3.91mm
INA28xAQDGKRQ1	VSSOP (8)	3.00mm × 3.00mm

(1) 要了解所有可用封装，请参见数据表末尾的封装选项附录。

详细方框图



目录

4 修订历史记录

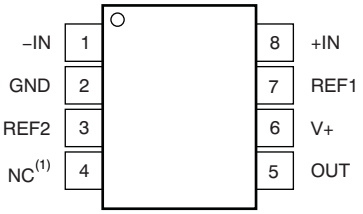
Changes from Revision A (July 2015) to Revision B **Page**

Changes from Original (March 2012) to Revision A **Page**

- 已将 VSSOP 封装从产品预览改为量产数据 ... 1
- 已将数据表标题从*高精度、宽共模范围、双向电流监控器零漂移系列*改为 *INA28x-Q1 汽车级、–14V 至 +80V、双向、高精度、低侧/高侧、电压输出、分流监控器* ... 1
- 已添加 DGK (VSSOP) 封装至数据表 ... 1
- 已更改*应用* ... 1
- 更改了首页图 ... 1
- Added *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 3
- Added RVRR as symbol for reference rejection ratio ... 5
- Changed order of figures in *Typical Characteristics* section ... 7
- Changed Figure 16 ... 9
- Changed V_{DRIVE} condition in Figure 20 and Figure 21 ... 10
- Added functional block diagram ... 13
- Changed Figure 32 and Figure 33 ... 15
- Changed Figure 34 and Figure 35 ... 16
- Changed Figure 36 and Figure 37 ... 17
- Changed Figure 38 ... 17
- Changed *Reference Common-Mode Rejection* to *Reference Voltage Rejection Ratio* ... 18
- Changed R_{CMR} to RVRR in Table 1 and Table 2 ... 19
- Changed Figure 39 ... 20
- Changed Figure 40 ... 21
- Changed Figure 42 ... 23

5 Pin Configuration and Functions

D and DGK Package
8-Pin SOIC and VSSOP
Top View



(1) NC: This pin is not internally connected. The NC pin should either be left floating or connected to GND.

Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	–IN	Analog input	Connection to negative side of shunt resistor.
2	GND	Analog	Ground
3	REF2	Analog input	Reference voltage, 0 V to V+. See *Reference Pin Connection Options* section for connection options.
4	NC	—	This pin is not internally connected. The NC pin should either be left floating or connected to GND.
5	OUT	Analog output	Output voltage
6	V+	Analog	Power supply, 2.7 V to 18 V
7	REF1	Analog input	Reference voltage, 0 V to V+. See *Reference Pin Connection Options* section for connection options.
8	+IN	Analog input	Connection to positive side of shunt resistor.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range, unless otherwise noted.(1)

		MIN	MAX	UNIT
Supply voltage, V+			18	V
Analog inputs, V_{+IN}, $V_{–IN}$(2)	Differential (V_{+IN}) – ($V_{–IN}$)(3)	–5	5	V
	Common-Mode	–14	80	V
REF1, REF2, OUT		GND–0.3	(V+) + 0.3	V
Input current into any pin			5	mA
Junction temperature			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) V_{+IN} and $V_{–IN}$ are the voltages at the +IN and –IN pins, respectively.
(3) Input voltages must not exceed common-mode rating.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002(1)	±2000	V
		Charged device model (CDM), per AEC Q100-011	±750	

(1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CM}	Common-mode input voltage		12		V
V+	Operating supply voltage		5		V
T_A	Operating free-air temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC(1)		INA28x-Q1		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	134.9	164.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	72.9	56.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	61.3	85.0	°C/W
ψ_{JT}	Junction-to-top characterization parameter	18.9	6.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	54.3	83.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

at T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
INPUT							
V_{OS}	Offset Voltage, RTI(1)	V_{SENSE} = 0 mV			±20	±70	µV
dV_{OS}/dT	vs Temperature	T_A = –40°C to 125°C			±0.3	±1.5	µV/°C
PSRR	vs Power Supply	V_S = 2.7 V to 18 V, V_{SENSE} = 0 mV			3		µV/V
V_{CM}	Common-Mode Input Range	T_A = –40°C to 125°C		–14		+80	V
CMRR	Common-Mode Rejection	V_{+IN} = –14 V to 80 V, V_{SENSE} = 0 mV T_A = –40°C to 125°C		120	140		dB
I_B	Input Bias Current per Pin(2)	V_{SENSE} = 0 mV			25		µA
I_{OS}	Input Offset Current	V_{SENSE} = 0 mV			1		µA
	Differential Input Impedance				6		kΩ
REFERENCE INPUTS							
	Reference Input Gain				1		V/V
	Reference Input Voltage Range(3)			0		V_{GND} + 9	V
	Divider Accuracy(4)				±0.2%	±0.5%	
RVRR	Reference Voltage Rejection Ratio ($V_{REF}1$ = $V_{REF}2$ = 40 mV to 9 V, V+ = 18 V)	INA282-Q1			±25	±75	µV/V
			T_A = –40°C to 125°C		0.055		µV/V/°C
		INA283-Q1			±13	±30	µV/V
			T_A = –40°C to 125°C		0.040		µV/V/°C
		INA284-Q1			±6	±25	µV/V
			T_A = –40°C to 125°C		0.015		µV/V/°C
		INA285-Q1			±4	±10	µV/V
			T_A = –40°C to 125°C		0.010		µV/V/°C
		INA286-Q1			±17	±45	µV/V
			T_A = –40°C to 125°C		0.040		µV/V/°C
GAIN(5) (GND + 0.5 V ≤ V_{OUT} ≤ (V+) – 0.5 V; V_{REF1} = V_{REF2} = (V+) / 2 for all devices)							
G	Gain	INA282-Q1, V+ = 5 V			50		V/V
		INA283-Q1, V+ = 5 V			200		V/V
		INA284-Q1, V+ = 5 V			500		V/V
		INA285-Q1, V+ = 5 V			1000		V/V
		INA286-Q1, V+ = 5 V			100		V/V
	Gain Error	INA282-Q1, INA283-Q1, INA286-Q1			±0.4%	±1.4%	
		INA284-Q1, INA285-Q1			±0.4%	±1.6%	
		T_A = –40°C to 125°C			0.0008	0.005	%/°C

(1) RTI = referred-to-input.
(2) See typical characteristic graph Figure 7 .
(3) The average of the voltage on pins REF1 and REF2 must be between V_{GND} and the lesser of (V_{GND}+9 V) and V+.
(4) Reference divider accuracy specifies the match between the reference divider resistors using the configuration in Figure 36.
(5) See typical characteristic graph Figure 12.

Electrical Characteristics (continued)

at T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OUTPUT						
	Nonlinearity Error			±0.01%		
	Output Impedance			1.5		Ω
	Maximum Capacitive Load	No sustained oscillation		1		nF
VOLTAGE OUTPUT (6)						
	Swing to V+ Power-Supply Rail	V+ = 5 V, R_{LOAD} = 10 kΩ to GND T_A = –40°C to 125°C		(V+)–0.17	(V+)–0.4	V
	Swing to GND	T_A = –40°C to 125°C		GND+0.015	GND+0.04	V
FREQUENCY RESPONSE						
BW	Effective Bandwidth (7)	INA282-Q1		10		kHz
		INA283-Q1		10		
		INA284-Q1		4		
		INA285-Q1		2		
		INA286-Q1		10		
NOISE, RTI (1)						
	Voltage Noise Density	1 kHz		110		nV/√Hz
POWER SUPPLY						
V_S	Specified Voltage Range	T_A = –40°C to 125°C	2.7		18	V
I_Q	Quiescent Current			600	900	µA
TEMPERATURE RANGE						
Specified Range			–40		125	°C

(6) See typical characteristic graphs Figure 16 through Figure 18.
(7) See typical characteristic graph Figure 1 and the *Effective Bandwidth* section in the Applications Information.

6.6 Typical Characteristics

At T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

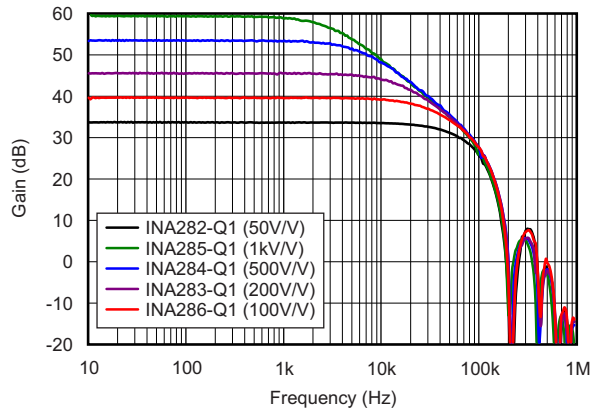


Figure 1. Gain vs Frequency

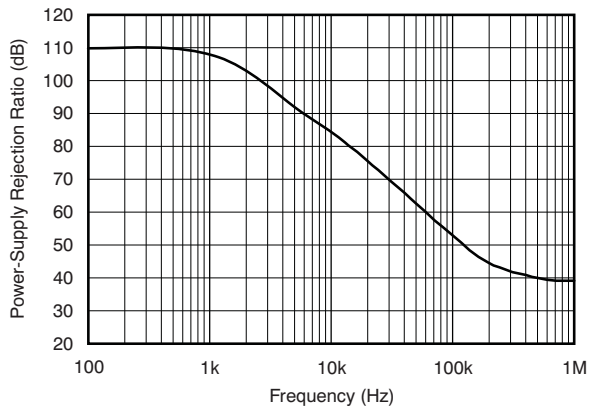


Figure 2. INA282-Q1 PSRR (RTI) vs Frequency

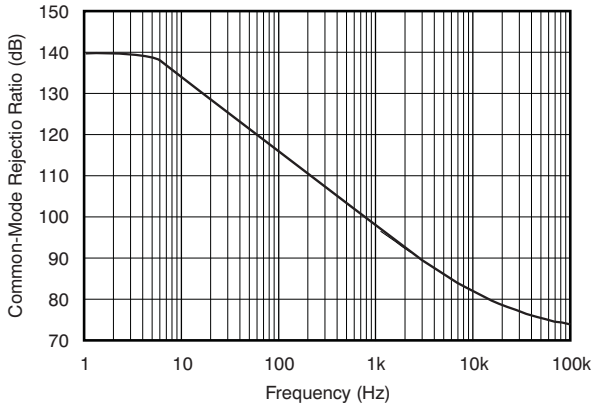


Figure 3. INA284-Q1 Common-Mode Rejection Ratio (RTI)

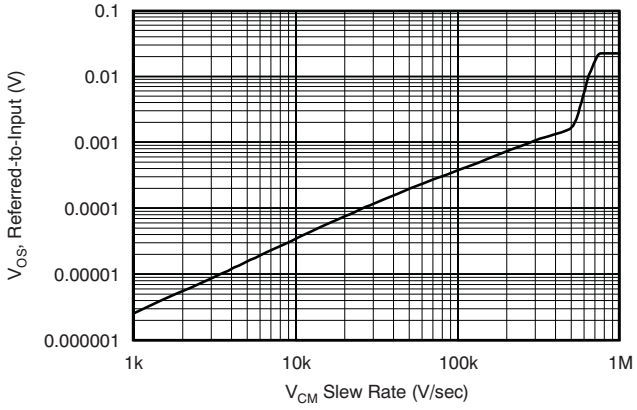


Figure 4. INA282-Q1 Common-Mode Slew Rate Induced Offset

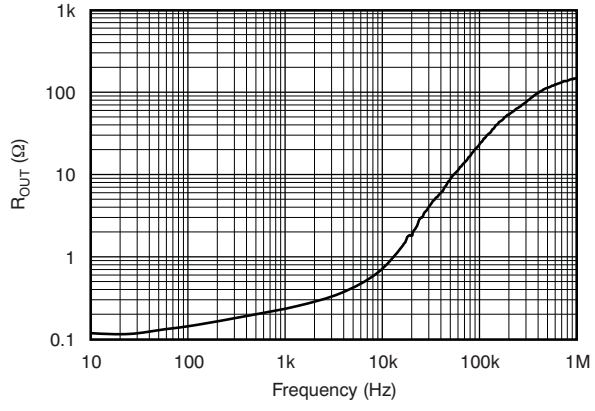


Figure 5. INA286-Q1 Output Impedance vs Frequency

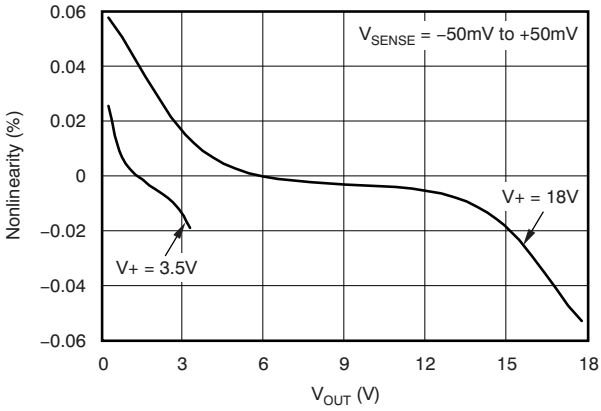


Figure 6. INA282-Q1 Typical Nonlinearity vs Output Voltage

Typical Characteristics (continued)

At T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

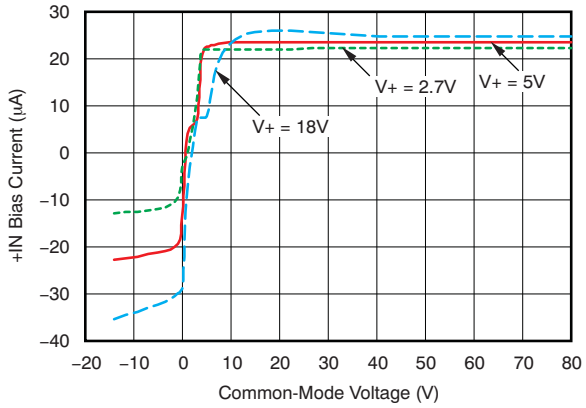


Figure 7. INA283-Q1 +IN BIAS Current vs Common-Mode Voltage

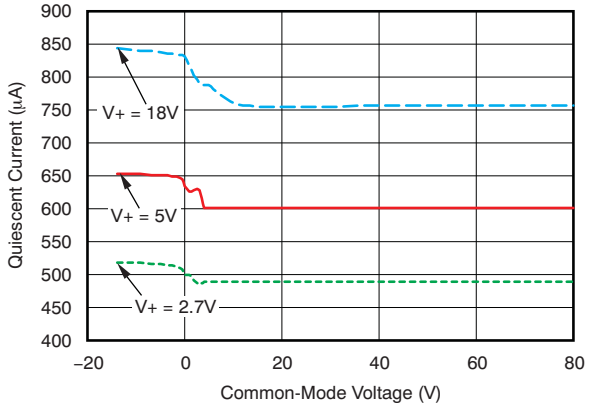


Figure 8. INA283-Q1 Quiescent Current vs Common-Mode Voltage

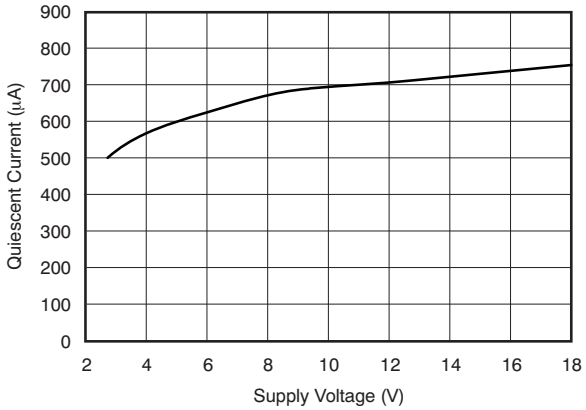


Figure 9. Quiescent Current vs Supply Voltage

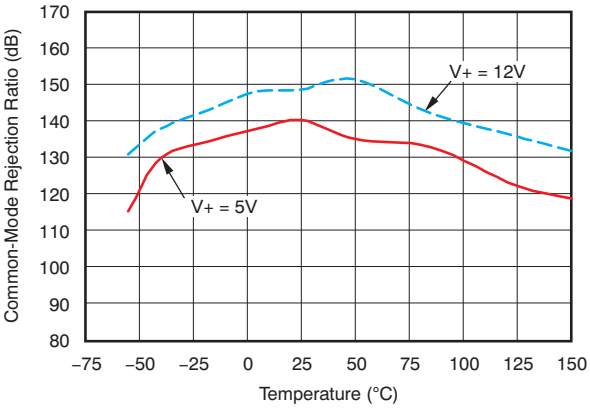


Figure 10. Common-Mode Rejection Ratio vs Temperature

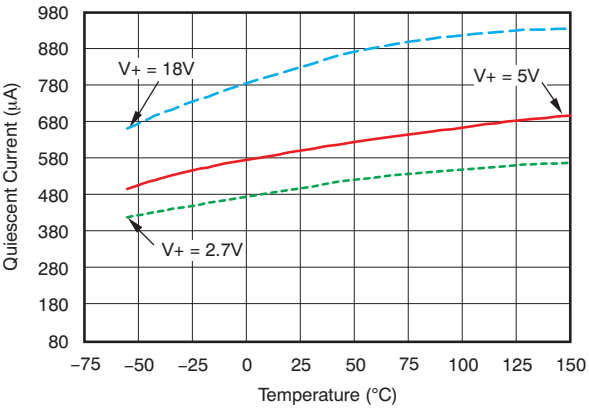


Figure 11. Quiescent Current vs Temperature

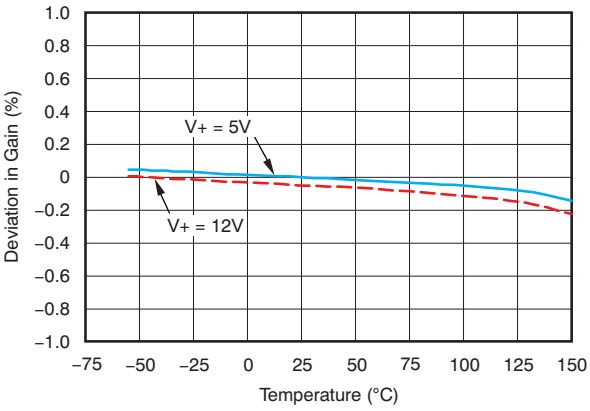


Figure 12. Deviation in Gain vs Temperature

Typical Characteristics (continued)

At T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

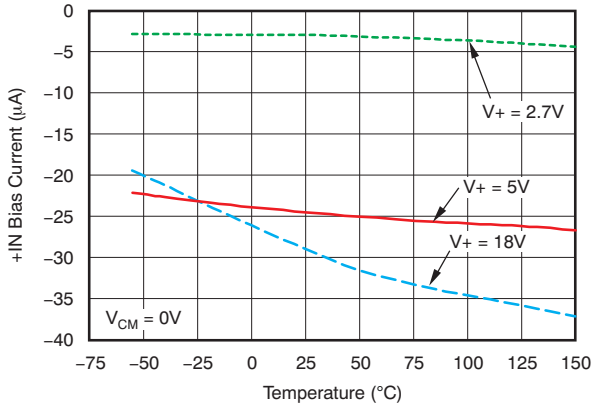


Figure 13. +IN BIAS Current vs Temperature

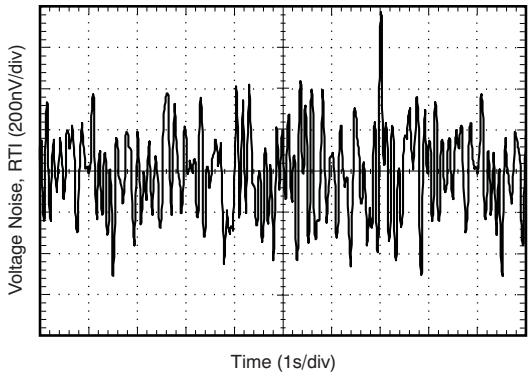


Figure 14. INA282-Q1 0.1-Hz to 10-Hz Voltage Noise, RTI

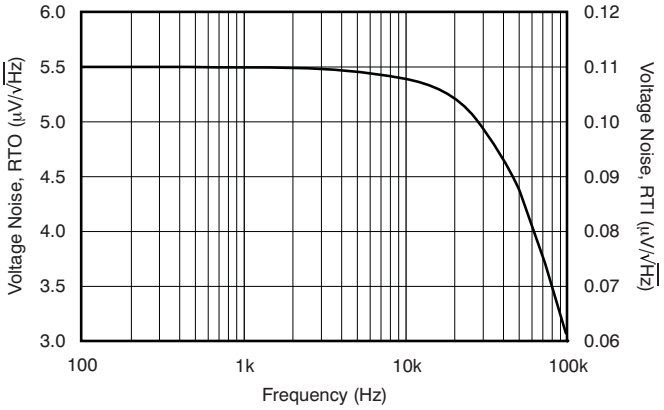


Figure 15. INA282-Q1 Voltage Noise vs Frequency

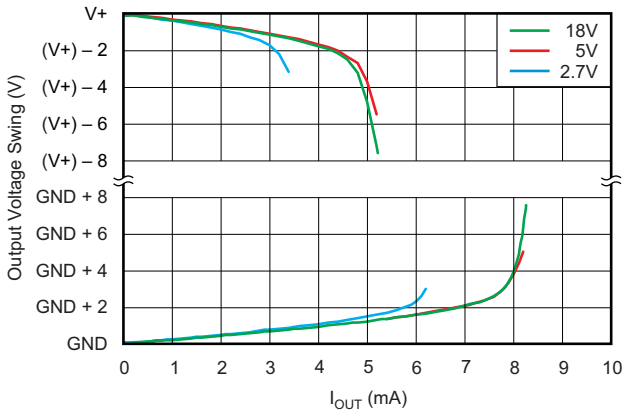


Figure 16. INA284-Q1 Output Voltage Swing vs Output Current

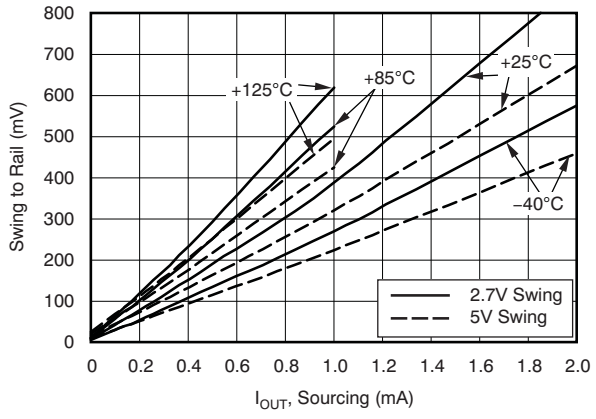


Figure 17. INA283-Q1 Swing to Rail vs Output Current

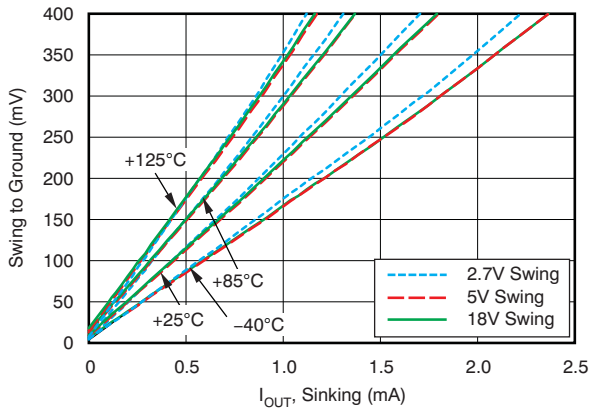


Figure 18. INA283-Q1 Swing to Ground vs Output Current

Typical Characteristics (continued)

At T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

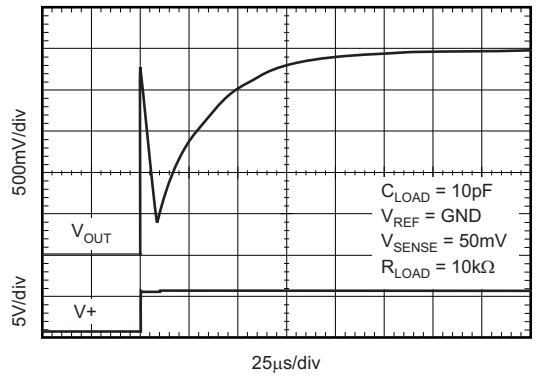


Figure 19. Start-Up Transient Response

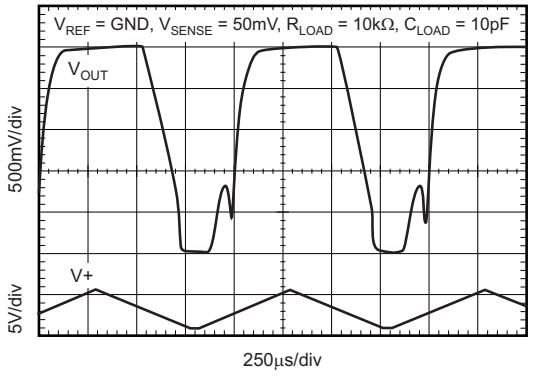


Figure 20. Start-Up Transient Response

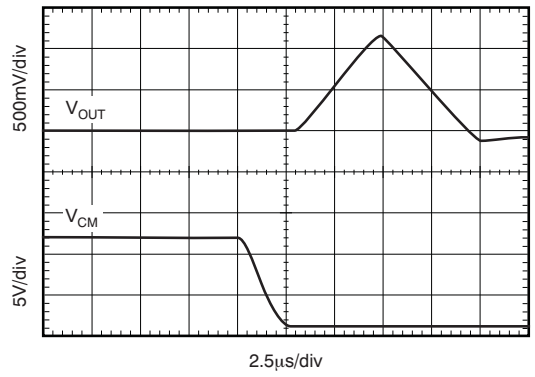


Figure 21. 12-V Common-Mode Step Response

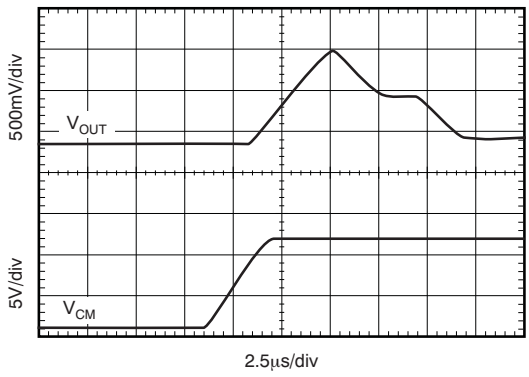


Figure 22. 12-V Common-Mode Step Response

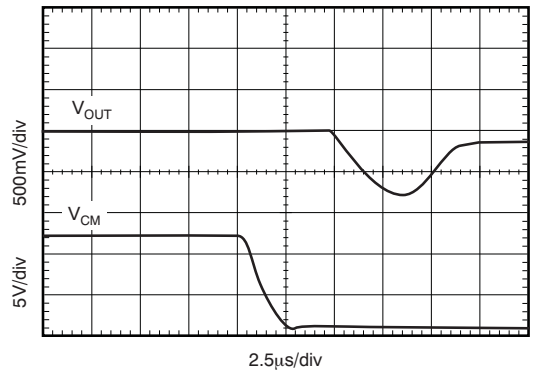


Figure 23. 12-V Common-Mode Step Response

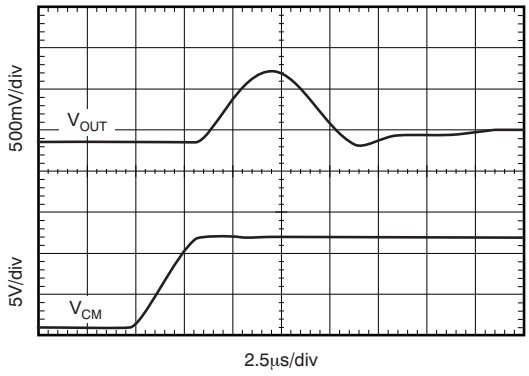


Figure 24. 12-V Common-Mode Step Response

Typical Characteristics (continued)

At T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

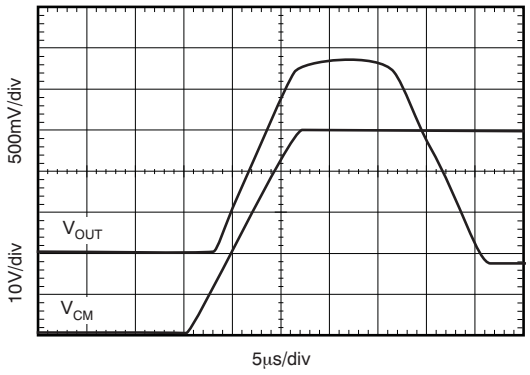


Figure 25. 50-V Common-Mode Step Response

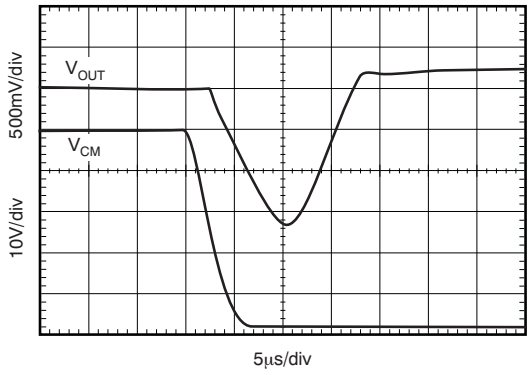


Figure 26. 50-V Common-Mode Step Response

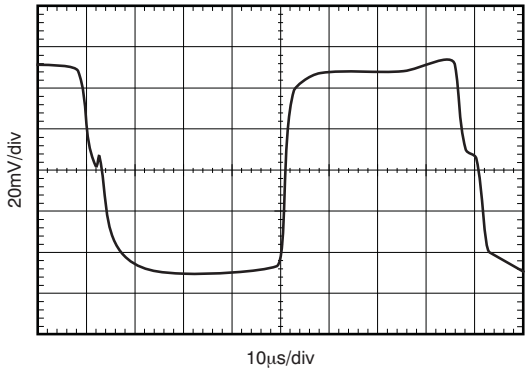


Figure 27. 100-mV Step Response

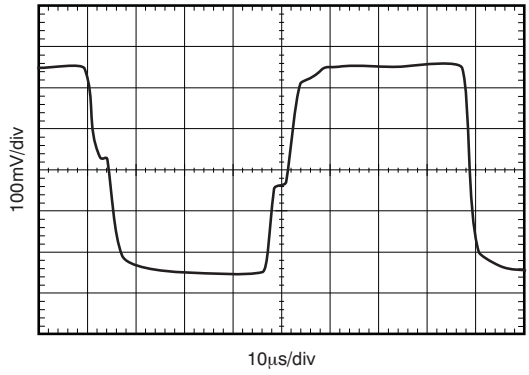


Figure 28. 500-mV Step Response

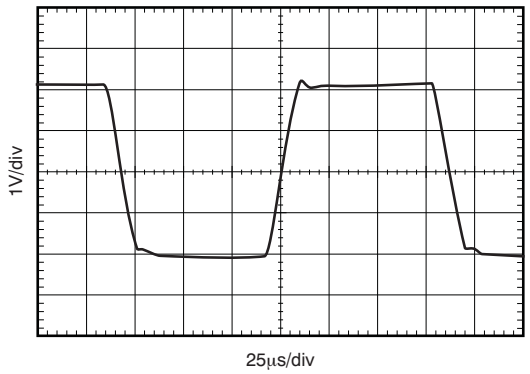


Figure 29. 4-V Step Response

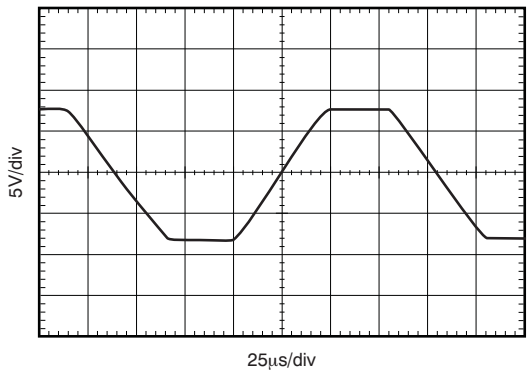


Figure 30. 17-V Step Response

Typical Characteristics (continued)

At T_A = 25°C, V+ = 5 V, V_{+IN} = 12 V, V_{REF1} = V_{REF2} = 2.048 V referenced to GND, and V_{SENSE} = V_{+IN} – $V_{–IN}$, unless otherwise noted.

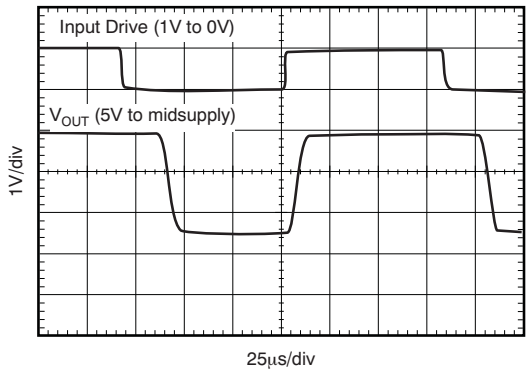


Figure 31. Input Overload

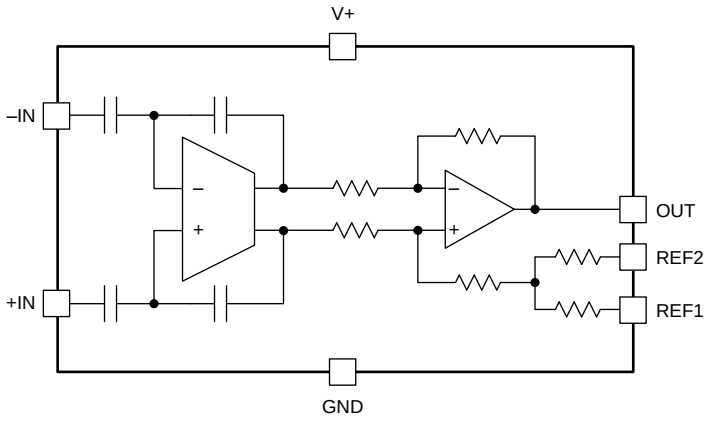
7 Detailed Description

7.1 Overview

The INA28x-Q1 family of voltage output current-sensing amplifiers are specifically designed to accurately measure voltages developed across current-sensing resistors on common-mode voltages that far exceed the supply voltage powering the devices. This family features a common-mode range that extends 14 V less than the negative supply rail, as well as up to 80 V, allowing for either low-side or high-side current sensing while the device is powered from supply voltages as low as 2.7 V.

The zero-drift topology enables high-precision measurements with maximum input offset voltages as low as 70 µV with a maximum temperature contribution of 1.5 µV/°C over the full temperature range of –40°C to 125°C.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Selecting R_S

The zero-drift offset performance of the INA28x-Q1 family offers several benefits. Most often, the primary advantage of the low offset characteristic enables lower full-scale drops across the shunt. For example, nonzero-drift, current-shunt monitors typically require a full-scale range of 100 mV. The INA28x-Q1 family gives equivalent accuracy at a full-scale range on the order of 10 mV. This accuracy reduces shunt dissipation by an order of magnitude, with many additional benefits. Alternatively, applications that must measure current over a wide dynamic range can take advantage of the low offset on the low end of the measurement. Most often, these applications can use the lower gains of the INA282-Q1, INA286-Q1, or INA283-Q1 to accommodate larger shunt drops on the upper end of the scale. For instance, an INA282-Q1 operating on a 3.3-V supply can easily handle a full-scale shunt drop of 55 mV, with only 70 µV of offset.

7.3.2 Effective Bandwidth

The extremely high DC CMRR of the INA28x-Q1 results from the switched capacitor input structure. Because of this architecture, the INA28x-Q1 exhibits discrete time system behaviors as illustrated in the gain versus frequency graph of Figure 3 and the step response curves of Figure 21 through Figure 28. The response to a step input depends somewhat on the phase of the internal INA28x-Q1 clock when the input step occurs. It is possible to overload the input amplifier with a rapid change in input common-mode voltage (see Figure 4). Errors as a result of common-mode voltage steps and/or overload situations typically disappear within 15 µs after the disturbance is removed.

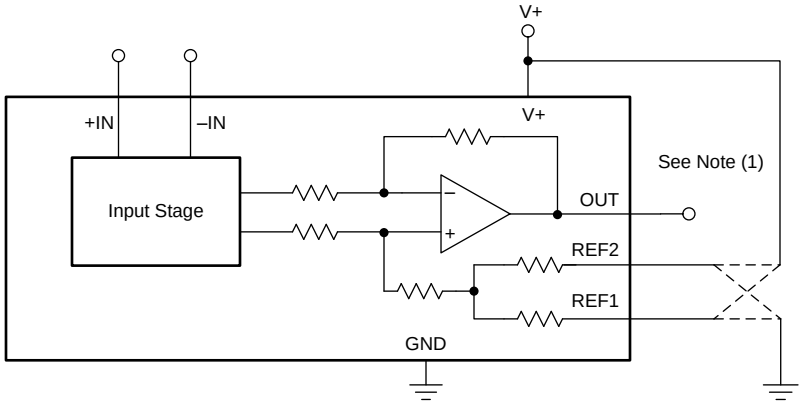
7.3.3 Transient Protection

The –14-V to 80-V common-mode range of the INA28x-Q1 is ideal for withstanding automotive fault conditions that range from 12-V battery reversal up to 80-V transients; no additional protective components are needed up to those levels. In the event that the INA28x-Q1 is exposed to transients on the inputs in excess of its ratings, then external transient absorption with semiconductor transient absorbers (Zener or *Transzorbs*) will be necessary. Use of MOVs or VDRs is not recommended except when they are used in addition to a semiconductor transient absorber. Select the transient absorber such that it cannot allow the INA28x-Q1 to be exposed to transients greater than 80 V (that is, allow for transient absorber tolerance, as well as additional voltage as a result of transient absorber dynamic impedance). Despite the use of internal zener-type electrostatic discharge (ESD) protection, the INA28x-Q1 does not lend itself to using external resistors in series with the inputs without degrading gain accuracy.

7.4 Device Functional Modes

7.4.1 Reference Pin Connection Options

Figure 32 illustrates a test circuit for reference divider accuracy. The output of the INA28x-Q1 can be connected for unidirectional or bidirectional operation. Neither the REF1 pin nor the REF2 pin may be connected to any voltage source lower than GND or higher than V+, and that the effective reference voltage (REF1 + REF2)/2 must be 9 V or less. This parameter means that the V+ reference output connection shown in Figure 34 is not allowed for V+ greater than 9 V. However, the split-supply reference connection shown in Figure 36 is allowed for all values of V+ up to 18 V.



(1) Reference divider accuracy is determined by measuring the output with the reference voltage applied to alternate reference resistors, and calculating a result such that the amplifier offset is cancelled in the final measurement.

Figure 32. Test Circuit for Reference Divider Accuracy

7.4.1.1 Unidirectional Operation

Unidirectional operation allows the INA28x-Q1 to measure currents through a resistive shunt in one direction. In the case of unidirectional operation, the output could be set at the negative rail (near ground, and the most common connection) or at the positive rail (near V+) when the differential input is 0V. The output moves to the opposite rail when a correct polarity differential input voltage is applied.

The required polarity of the differential input depends on the output voltage setting. If the output is set at the positive rail, the input polarity must be negative to move the output down. If the output is set at ground, the polarity is positive to move the output up.

The following sections describe how to configure the output for unidirectional operation.

7.4.1.1.1 Ground Referenced Output

When using the INA28x-Q1 in this mode, both reference inputs are connected to ground; this configuration takes the output to the negative rail when there is 0V differential at the input (as Figure 33 shows).

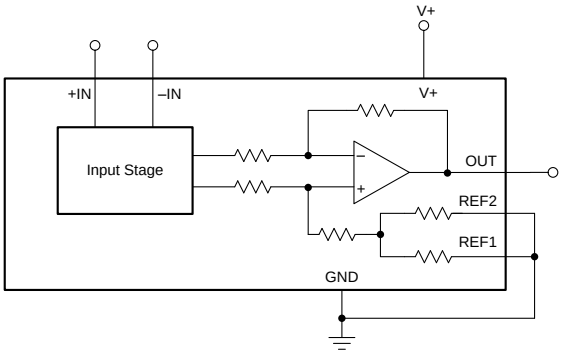


Figure 33. Ground Referenced Output

Device Functional Modes (continued)

7.4.1.1.2 V+ Referenced Output

This mode is set when both reference pins are connected to the positive supply. It is typically used when a diagnostic scheme requires detection of the amplifier and the wiring before power is applied to the load (as shown in Figure 34).

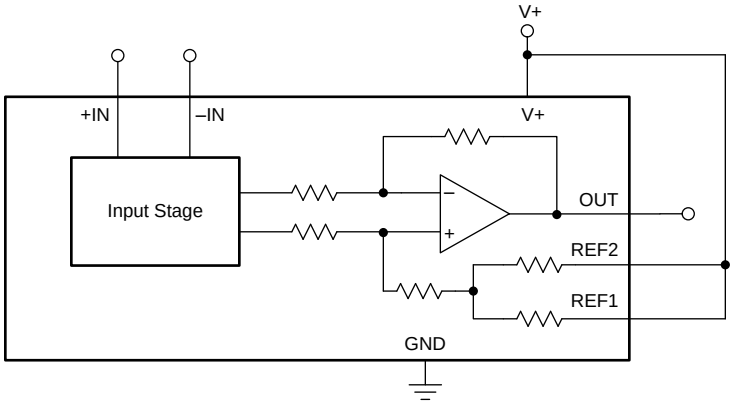


Figure 34. V+ Referenced Output

7.4.1.2 Bidirectional Operation

Bidirectional operation allows the INA28x-Q1 to measure currents through a resistive shunt in two directions. In this case, the output can be set anywhere within the limits of what the reference inputs allow (that is, from 0 V to 9 V, but never to exceed the supply voltage). Typically, it is set at half-scale for equal range in both directions. In some cases, however, it is set at a voltage other than half-scale when the bidirectional current is nonsymmetrical.

The quiescent output voltage is set by applying voltage(s) to the reference inputs. REF1 and REF2 are connected to internal resistors that connect to an internal offset node. There is no operational difference between the pins.

7.4.1.2.1 External Reference Output

Connecting both pins together and to a reference produces an output at the reference voltage when there is no differential input; this configuration is illustrated in Figure 35. The output moves down from the reference voltage when the input is negative relative to the –IN pin and up when the input is positive relative to the –IN pin. This technique is the most accurate way to bias the output to a precise voltage.

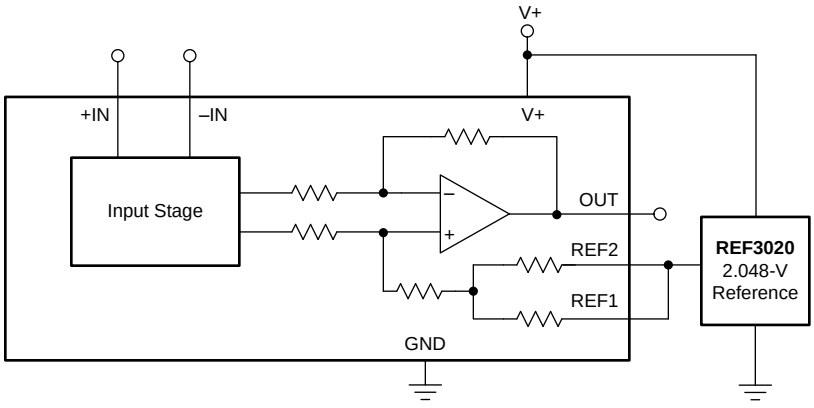


Figure 35. External Reference Output

Device Functional Modes (continued)

7.4.1.2.2 Splitting the Supply

By connecting one reference pin to V+ and the other to the ground pin, the output is set at half of the supply when there is no differential input, as shown in Figure 36. This method creates a midscale offset that is ratiometric to the supply voltage; thus, if the supply increases or decreases, the output remains at half the supply.

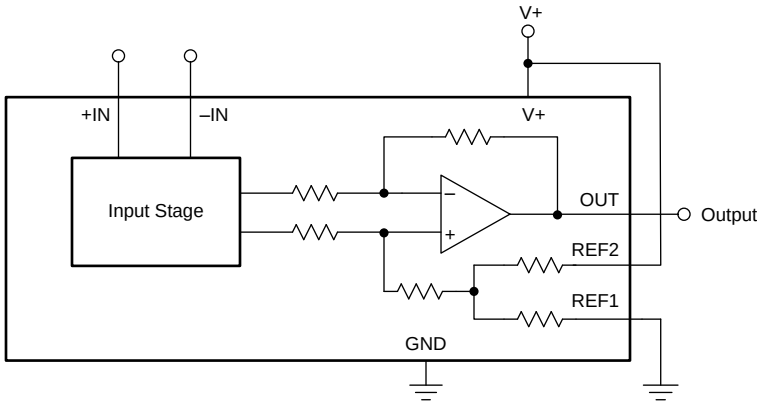


Figure 36. Split-Supply Output

7.4.1.2.3 Splitting an External Reference

In this case, an external reference is divided by 2 with an accuracy of approximately 0.5% by connecting one REF pin to ground and the other REF pin to the reference (as Figure 37 illustrates).

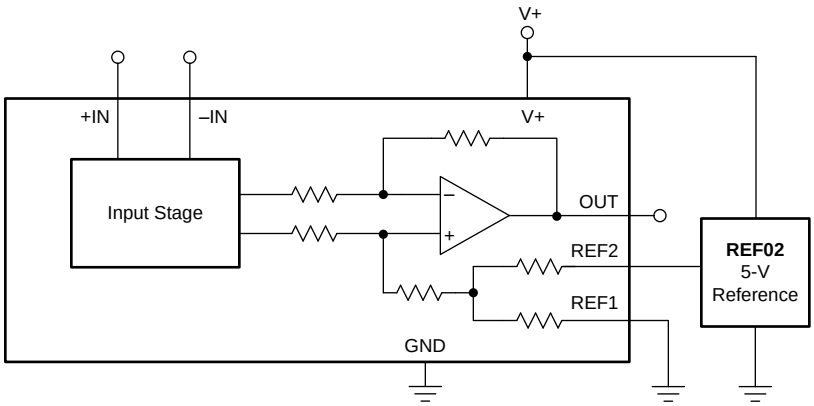


Figure 37. Split Reference Output

7.4.2 Shutdown

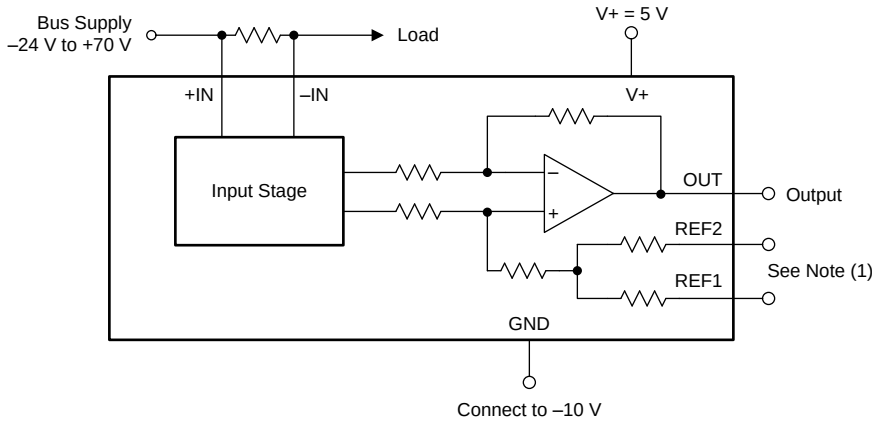
While the INA28x-Q1 family does not provide a shutdown pin, the quiescent current of 600 µA enables the device to be powered from the output of a logic gate. Take the gate low to shut down the INA28x-Q1 family devices.

7.4.3 Extended Negative Common-Mode Range

Using a negative power supply can extend the common-mode range 14 V more negative than the supply used. For instance, a –10 V supply allows up to –24-V negative common-mode. Remember to keep the total voltage between the GND pin and V+ pin to less than 18 V. The positive common-mode decreases by the same amount.

The reference input simplifies this type of operation because the output quiescent bias point is always based on the reference connections. Figure 38 shows a circuit configuration for common-mode ranges from –24 V to 70 V.

Device Functional Modes (continued)



(1) Connect the REF pins as desired; however, they cannot exceed 9 V greater than the GND pin voltage.

Figure 38. Circuit Configuration for Common-Mode Ranges from –24 V to 70 V

7.4.4 Calculating Total Error

The electrical specifications for the INA28x-Q1 family of devices include the typical individual errors terms such as gain error, offset error, and nonlinearity error. Total error including all of these individual error components is not specified in the *Electrical Characteristics* table. To accurately calculate the expected error of the device, the operating conditions of the device must first be known. Some current shunt monitors specify a total error in the product data sheet. However, this total error term is accurate under only one particular set of operating conditions. Specifying the total error at this one point has little practical value because any deviation from these specific operating conditions no longer yields the same total error value. This section discusses the individual error sources, with information on how to apply them to calculate the total error value for the device under any normal operating conditions.

The typical error sources that have the largest impact on the total error of the device are input offset voltage, common-mode rejection ratio, gain error, and nonlinearity error. For the INA28x-Q1, an additional error source referred to as *reference voltage rejection ratio* is also included in the total error value.

The nonlinearity error of the INA28x-Q1 is relatively low compared to the gain error specification. This low error results in a gain error that can be expected to be relatively constant throughout the linear input range of the device. While the gain error remains constant across the linear input range of the device, the error associated with the input offset voltage does not. As the differential input voltage developed across a shunt resistor at the input of the INA28x-Q1 decreases, the inherent input offset voltage of the device becomes a larger percentage of the measured input signal resulting in an increase in error in the measurement. This varying error is present among all current shunt monitors, given the input offset voltage ratio to the voltage being sensed by the device. The relatively low input offset voltages present in the INA28x-Q1 devices limit the amount of contribution the offset voltage has on the total error term.

The term *reference voltage rejection ratio* refers to the amount of error induced by applying a reference voltage to the INA28x-Q1 device that deviates from the inherent bias voltage present at the output of the first stage of the device. The output of the switched-capacitor network and first-stage amplifier has an inherent bias voltage of approximately 2.048 V. Applying a reference voltage of 2.048 V to the INA28x-Q1 reference pins results in no additional error term contribution. Applying a voltage to the reference pins that differs from 2.048 V creates a voltage potential in the internal difference amplifier, resulting in additional current flowing through the resistor network. As a result of resistor tolerances, this additional current flow causes additional error at the output because of resistor mismatches. Additionally, as a result of resistor tolerances, this additional current flow causes additional error at the output based on the common-mode rejection ratio of the output stage amplifier. This error term is referred back to the input of the device as additional input offset voltage. Increasing the difference between the 2.048-V internal bias and the external reference voltage results in a higher input offset voltage. Also, as the error at the output is referred back to the input, there is a larger impact on the input-referred offset, V_{OS}, for the lower-gain versions of the device.

Device Functional Modes (continued)

Two examples are provided that detail how different operating conditions can affect the total error calculations. Typical and maximum calculations are shown as well, to provide the user more information on how much error variance is present from device to device.

7.4.4.1 Example 1 INA282-Q1

Table 1. V+ = 5 V; V_{CM} = 12 V; V_{REF1} = V_{REF2} = 2.048 V; V_{SENSE} = 10 mV

TERM	SYMBOL	EQUATION	TYPICAL VALUE	MAXIMUM VALUE
Initial input offset voltage	V_{OS}	—	20 µV	70 µV
Added input offset voltage because of common-mode voltage	V_{OS_CM}	$\frac{1}{10^{\left(\frac{CMRR\_dB}{20}\right)}} \times (V_{CM} - 12V)$	0 µV	0 µV
Added input offset voltage because of reference voltage	V_{OS_REF}	$RVRR \times (2.048\ V - V_{REF})$	0 µV	0 µV
Total input offset voltage	V_{OS_Total}	$\sqrt{(V_{OS})^2 + (V_{OS\_CM})^2 + (V_{OS\_REF})^2}$	20 µV	70 µV
Error from input offset voltage	Error_V_{OS}	$\frac{V_{OS\_Total}}{V_{SENSE}} \times 100$	0.20%	0.70%
Gain error	Error_Gain	—	0.40%	1.40%
Nonlinearity error	Error_Lin	—	0.01%	0.01%
Total error	—	$\sqrt{(Error\_V_{OS})^2 + (Error\_Gain)^2 + (Error\_Lin)^2}$	0.45%	1.56%

7.4.4.2 Example 2 INA286-Q1

Table 2. V+ = 5 V; V_{CM} = 24 V; V_{REF1} = V_{REF2} = 0 V; V_{SENSE} = 10 mV

TERM	SYMBOL	EQUATION	TYPICAL VALUE	MAXIMUM VALUE
Initial input offset voltage	V_{OS}	—	20 µV	70 µV
Added input offset voltage because of common-mode voltage	V_{OS_CM}	$\frac{1}{10^{\left(\frac{CMRR\_dB}{20}\right)}} \times (V_{CM} - 12V)$	1.2 µV	12 µV
Added input offset voltage because of reference voltage	V_{OS_REF}	$RVRR \times (2.048\ V - V_{REF})$	34.8 µV	92.2 µV
Total input offset voltage	V_{OS_Total}	$\sqrt{(V_{OS})^2 + (V_{OS\_CM})^2 + (V_{OS\_REF})^2}$	40.2 µV	116.4 µV
Error from input offset voltage	Error_V_{OS}	$\frac{V_{OS\_Total}}{V_{SENSE}} \times 100$	0.40%	1.16%
Gain error	Error_Gain	—	0.40%	1.40%
Nonlinearity error	Error_Lin	—	0.01%	0.01%
Total error	—	$\sqrt{(Error\_V_{OS})^2 + (Error\_Gain)^2 + (Error\_Lin)^2}$	0.57%	1.82%

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The INA28x-Q1 family of devices measure the voltage developed across a current-sensing resistor when current passes through it. The ability to drive the reference pins to adjust the functionality of the output signal is shown in multiple configurations.

8.1.1 Basic Connections

Figure 39 shows the basic connection of an INA28x-Q1 family device. Connect the input pins, +IN and –IN, as close as possible to the shunt resistor to minimize any resistance in series with the shunt resistance.

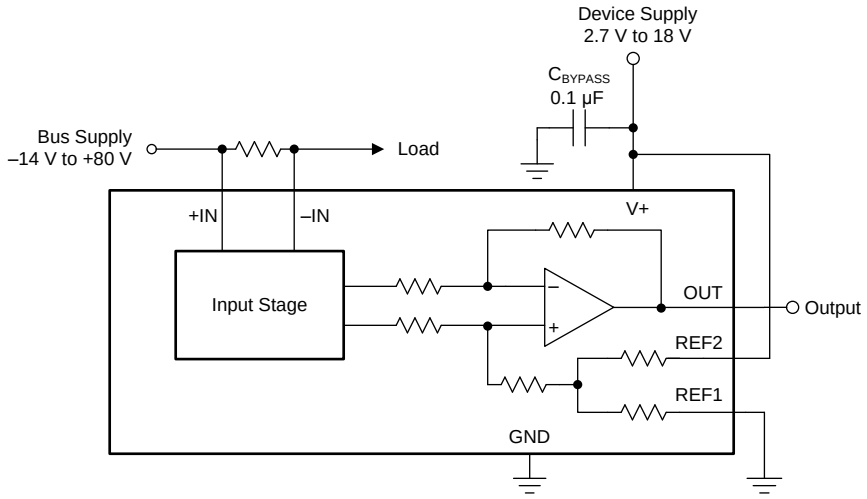


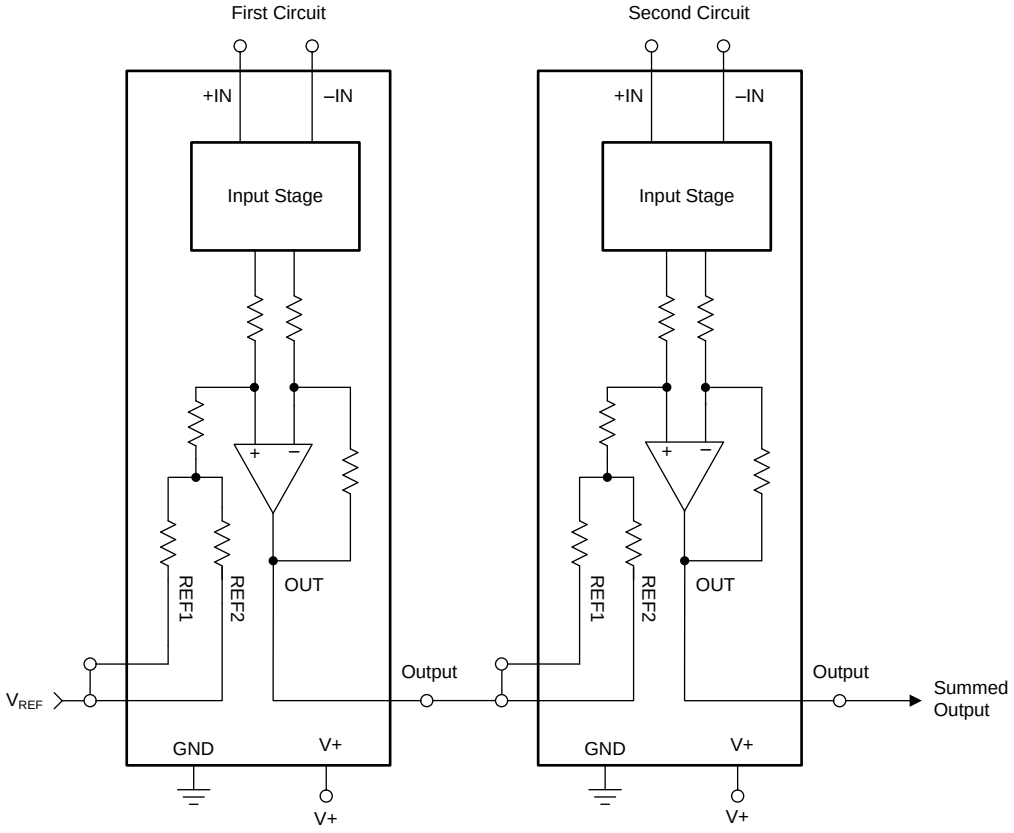
Figure 39. Basic Connections

Power-supply bypass capacitors are required for stability. Applications with noisy or high-impedance power supplies may require additional decoupling capacitors to reject power-supply noise. Connect bypass capacitors close to the device pins.

8.2 Typical Applications

8.2.1 Current Summing

The outputs of multiple INA28x-Q1 family devices are easily summed by connecting the output of one INA28x-Q1 family device to the reference input of a second INA28x-Q1 family device. The circuit configuration shown in Figure 39 is an easy way to achieve current summing.



NOTE: The voltage applied to the reference inputs must not exceed 9 V.

Figure 40. Summing the Outputs of Multiple INA28x-Q1 Family Devices

Typical Applications (continued)

8.2.1.1 Design Requirements

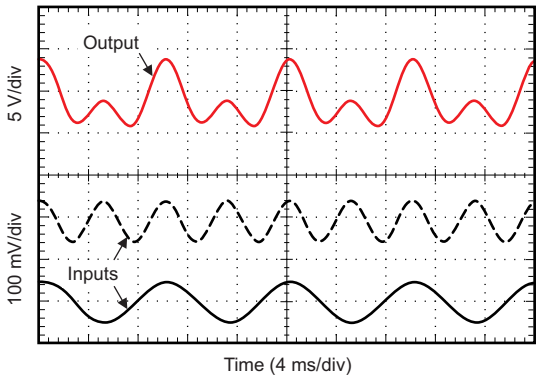
In order to sum multiple load currents, multiple INA28x-Q1 devices must be connected. Figure 40 shows summing for two devices. Summing beyond two devices is possible by repeating this connection. The reference input of the first INA28x-Q1 family device sets the output quiescent level for all the devices in the string.

8.2.1.2 Detailed Design Procedures

Connect the output of one INA28x-Q1 family device to the reference input of the next INA28x-Q1 family device in the chain. Use the reference input of the first circuit to set the reference of the final summed output. The currents sensed at each circuit in the chain are summed at the output of the last device in the chain.

8.2.1.3 Application Curve

Figure 41 shows an example output response of a summing configuration. The reference pins of the first circuit are connected to ground, and sine waves at different frequencies are applied to the two circuits to produce a summed output as shown. The sine wave voltage input for the first circuit is offset so that the whole wave is above GND.



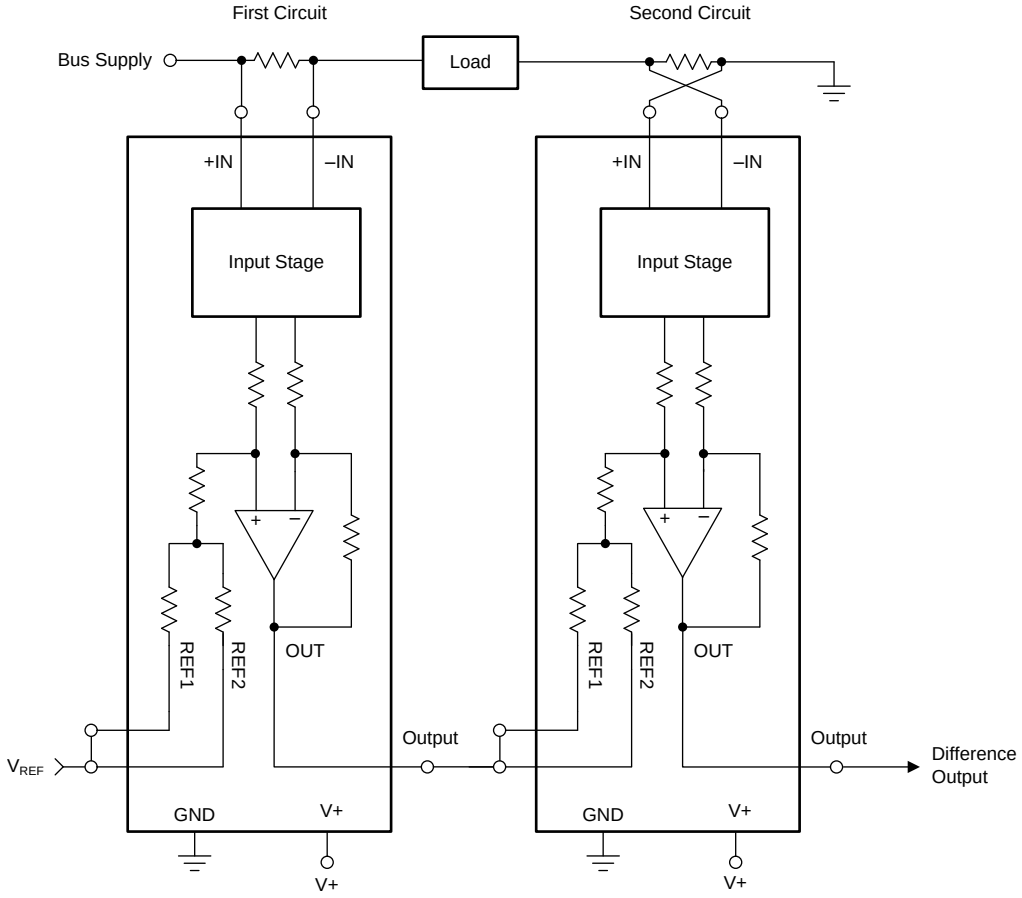
V_{REF} = 0 V

Figure 41. Current Summing Application Output Response

Typical Applications (continued)

8.2.2 Current Differencing

Occasionally, the need arises to confirm that the current into a load is identical to the current out of a load, usually as part of diagnostic testing or fault detection. This situation requires precision current differencing, which is the same as summing except that the two amplifiers have the inputs connected opposite of each other.



NOTE: The voltage applied to the reference inputs must not exceed 9 V.

Figure 42. Current Differencing Using an INA28x-Q1 Device

Typical Applications (continued)

8.2.2.1 Design Requirements

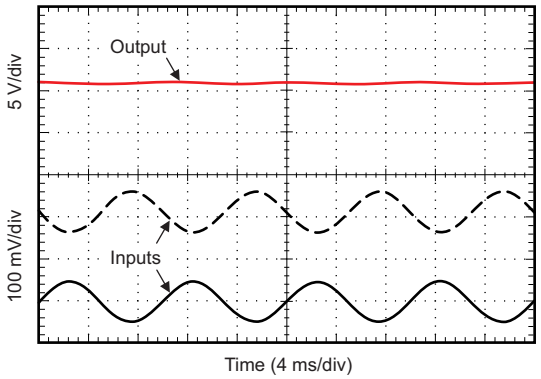
For current differencing, connect two INA28x-Q1 devices, and connect the inputs opposite to each other, as shown in Figure 42. The reference input of the first INA28x-Q1 family device sets the output quiescent level for all the devices in the string.

8.2.2.2 Detailed Design Procedure

Connect the output of one INA28x-Q1 family device to the reference input of the second INA28x-Q1 family device. The reference input of the first circuit sets the reference at the output. This circuit example is identical to the current summing example, except that the two shunt inputs are reversed in polarity. Under normal operating conditions, the final output is very close to the reference value and proportional to any current difference. This current differencing circuit is useful in detecting when current into and out of a load do not match.

8.2.2.3 Application Curves

Figure 43 shows an example output response of a difference configuration. The reference pins of the first circuit are connected to a reference voltage of 2.048 V. The inputs to each circuit is a 100-Hz sine wave, 180° out of phase with each other, resulting in a zero output as shown. The sine wave input to the first circuit is offset so that the input wave is completely above GND.



V_{REF} = 2.048 V

Figure 43. Current Differencing Application Output Response

9 Power Supply Recommendations

The INA28x-Q1 can make accurate measurements well outside of its own power-supply voltage, V+, because its inputs (+IN and –IN) may operate anywhere from –14 V to 80 V independent of V+. For example, the V+ power supply can be 5 V while the common-mode voltage being monitored by the shunt may be as high as 80 V. Of course, the output voltage range of the INA28x-Q1 is constrained by the supply voltage that powers it on V+. When the power to the INA28x-Q1 is off (that is, no voltage is supplied to the V+ pin), the input pins (+IN and –IN) are high impedance with respect to ground and typically leak less than ±1 µA over the full common-mode range of –14 V to 80 V.

10 Layout

10.1 Layout Guidelines

Connect the input pins to the sensing resistor using a Kelvin or 4-wire connection. This connection technique makes sure that only the current-sensing resistor impedance is detected between the input pins. Poor routing of the current-sensing resistor commonly results in additional resistance present between the input pins. Given the very low ohmic value of the current resistor, any additional high-current carrying impedance causes significant measurement errors.

Place the power-supply bypass capacitor as close as possible to the supply and ground pins. TI recommends a bypass capacitor with a value of 0.1 uF. Add additional decoupling capacitance to compensate for noisy or high-impedance power supplies.

10.2 Layout Example

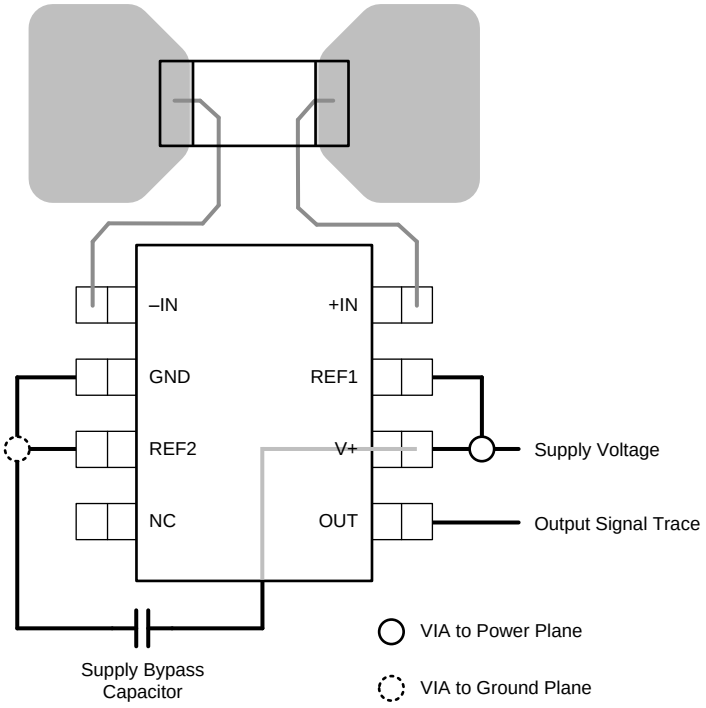


Figure 44. Layout Example

11 器件和文档支持

11.1 相关链接

下面的表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，以及样片或购买的快速访问。

表 3. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
INA282-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA283-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA284-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA285-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
INA286-Q1	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

11.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.3 商标

E2E is a trademark of Texas Instruments.
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11.4 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

11.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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邮寄地址： 上海市浦东新区世纪大道1568 号，中建大厦32 楼邮政编码： 200122

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA282AQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	11GF	Samples
INA282AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	282Q1	Samples
INA283AQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	11FF	Samples
INA283AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	283Q1	Samples
INA284AQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	11HF	Samples
INA284AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	284Q1	Samples
INA285AQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	11IF	Samples
INA285AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	285Q1	Samples
INA286AQDGKRQ1	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	11JF	Samples
INA286AQDRQ1	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	286Q1	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

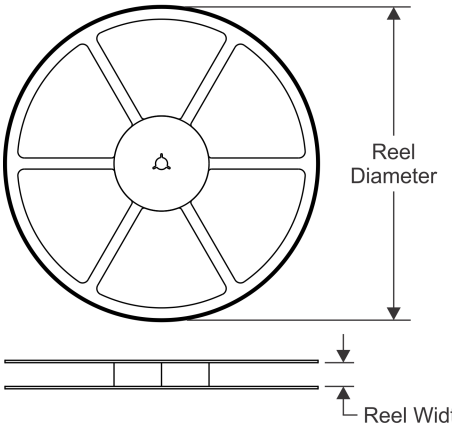
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

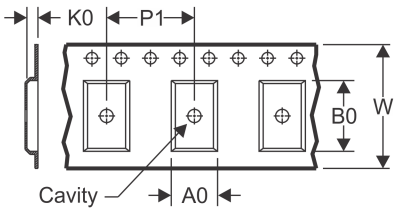
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

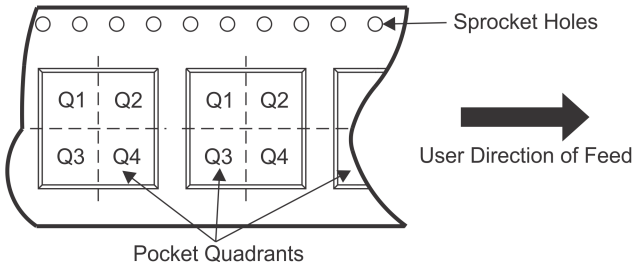


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

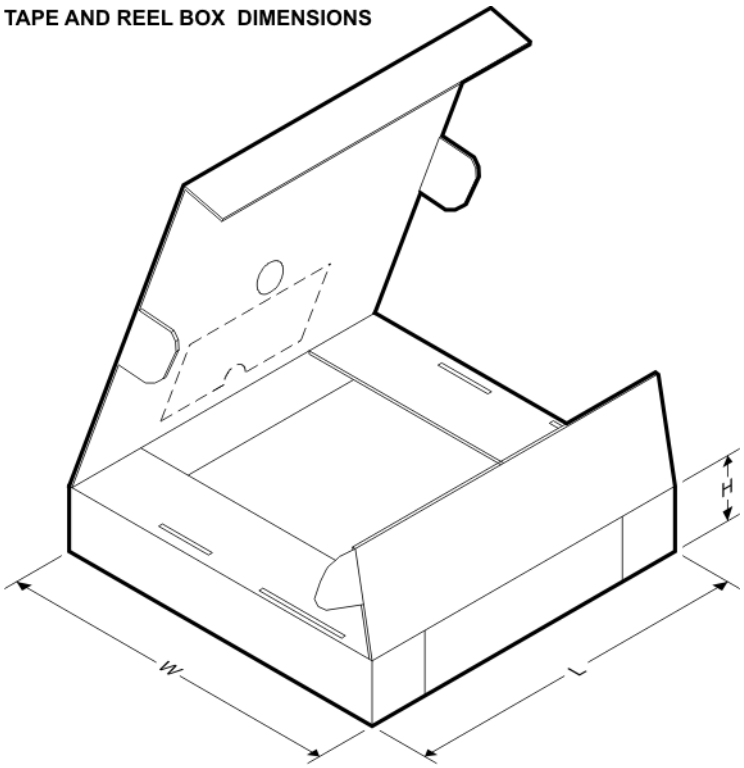
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

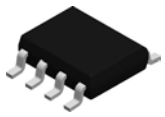
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA282AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA282AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA283AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA283AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA284AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA284AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA285AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA285AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
INA286AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
INA286AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA282AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA282AQDRQ1	SOIC	D	8	2500	853.0	449.0	35.0
INA283AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA283AQDRQ1	SOIC	D	8	2500	853.0	449.0	35.0
INA284AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA284AQDRQ1	SOIC	D	8	2500	853.0	449.0	35.0
INA285AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA285AQDRQ1	SOIC	D	8	2500	853.0	449.0	35.0
INA286AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
INA286AQDRQ1	SOIC	D	8	2500	853.0	449.0	35.0

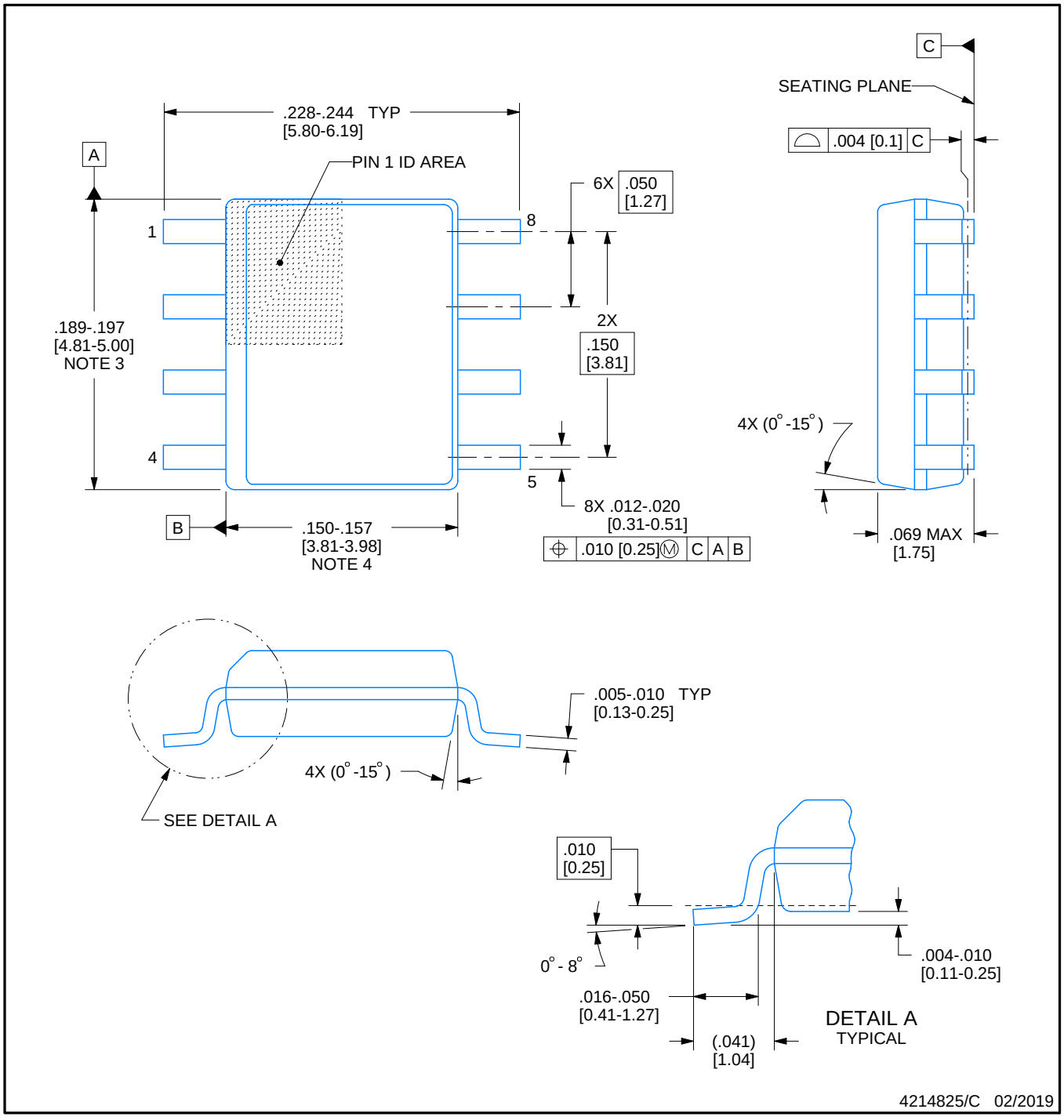


PACKAGE OUTLINE

D0008A

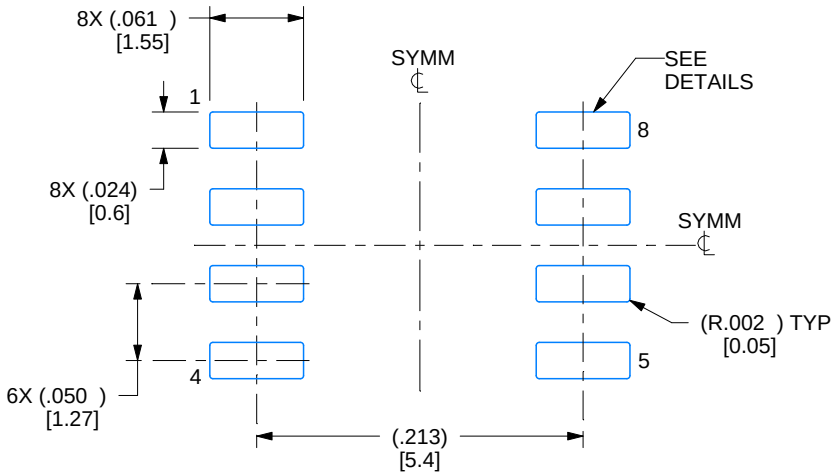
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

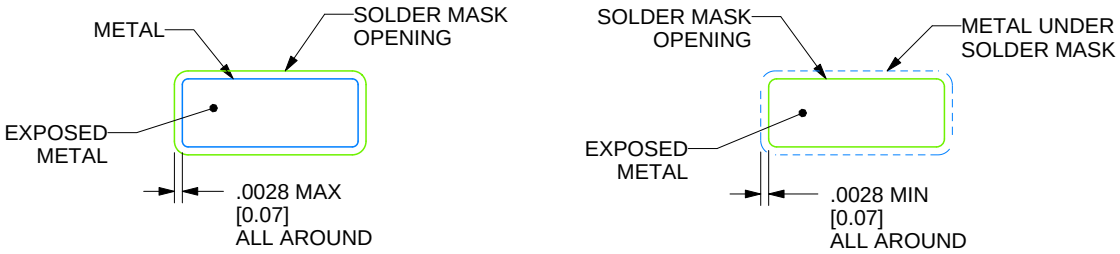


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

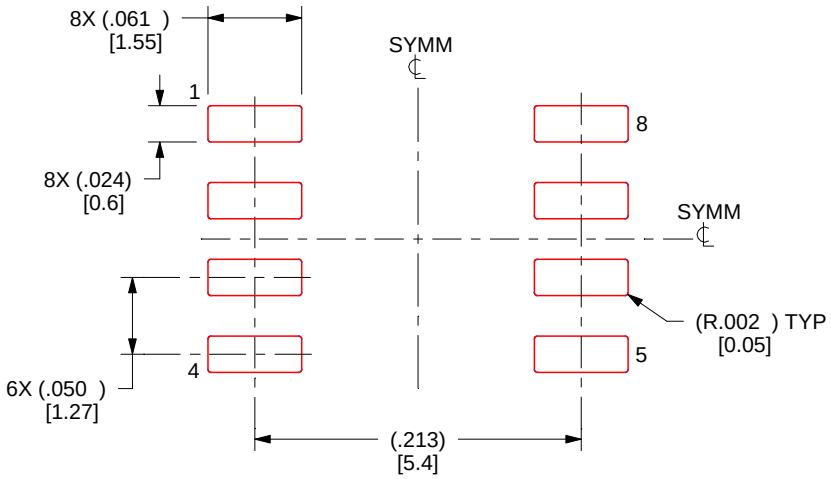
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



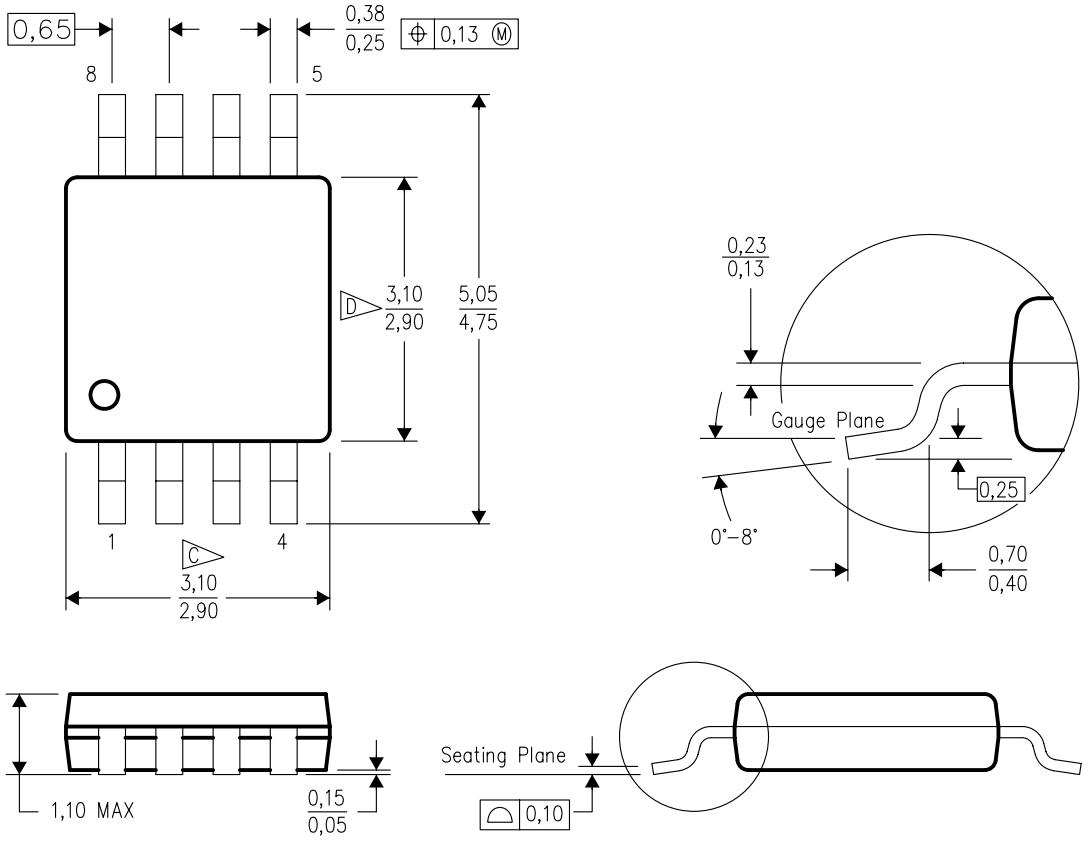
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

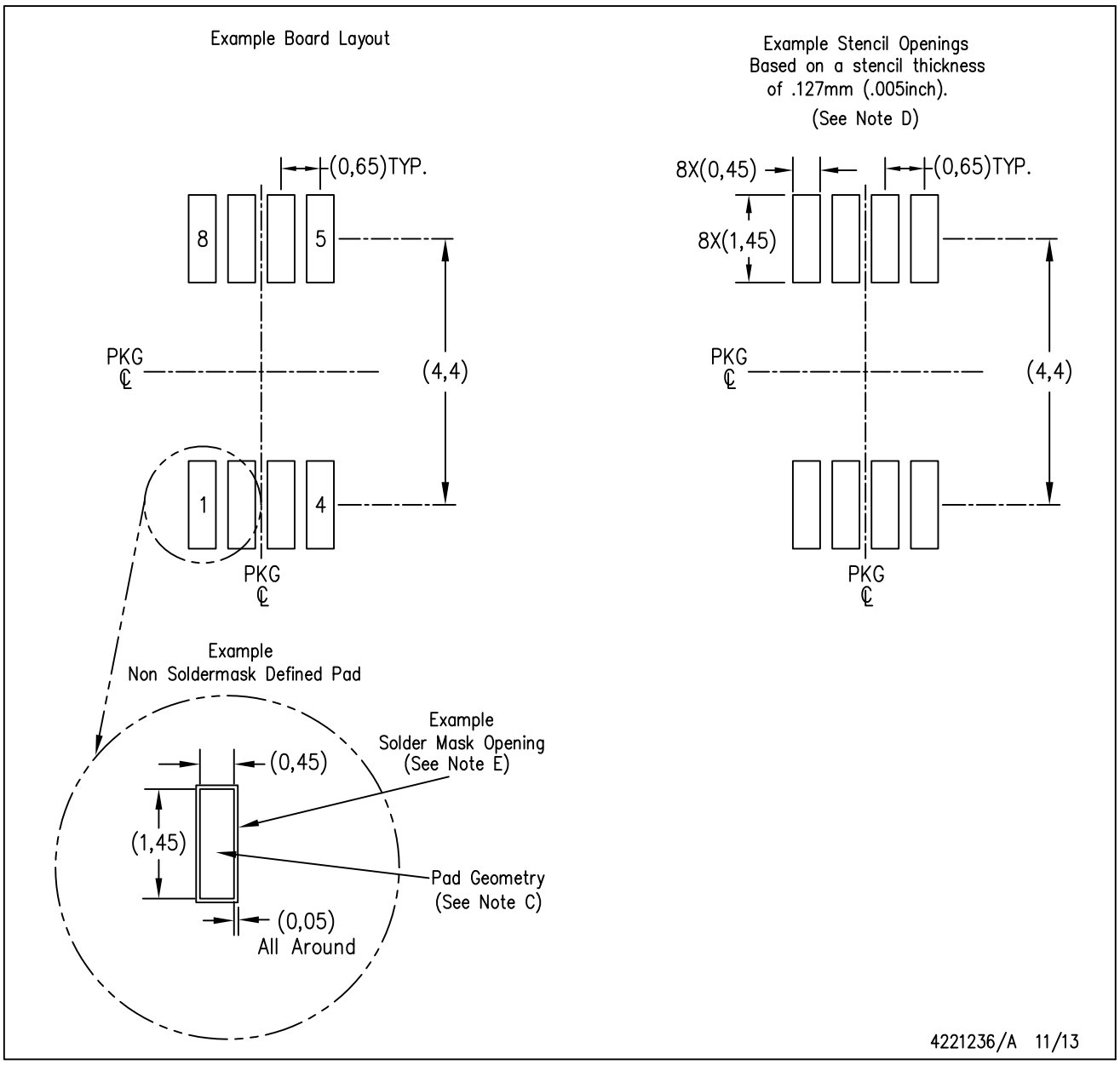
DGK (S–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



4073329/E 05/06

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO–187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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